



International Electronics Manufacturing Initiative

Surface Structure Effects of Sn electrodeposits on the Sn Whisker Growth



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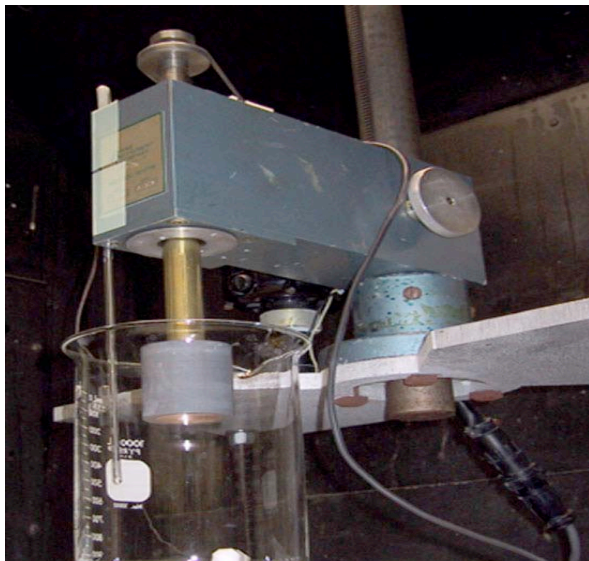
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- **Crystallographic orientation of Sn electrodeposits & hillocks - EBSD**
- **Examination of the effect of Sn oxide on whisker growth - Auger and SEM analyses**

- Objectives
 - Preferred orientation of Sn deposit (EBSD)
 - Growth direction of hillocks on Sn deposit (EBSD)
 - Sn surface oxide film effect on whisker growth (Auger & SEM)
- Samples
 - EBSD: Sn on phosphor bronze cantilever beam (16 μm thick)
 - Auger: Sn-3wt%Cu on pyrophosphate copper coupon (15 μm thick)

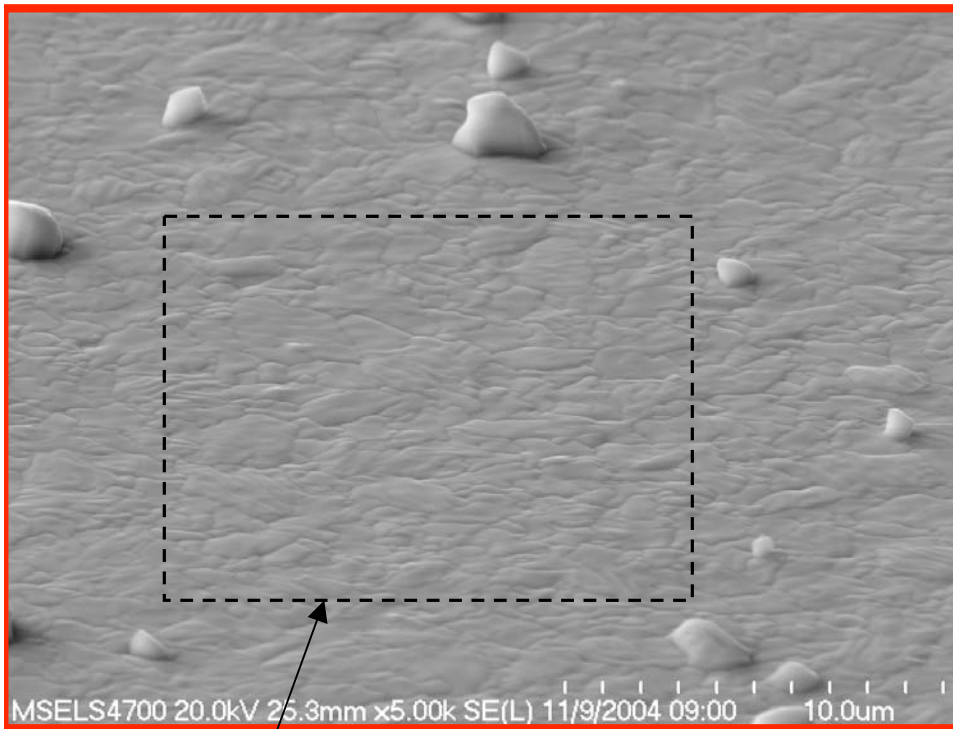


- Plating Conditions
 - Commercial bright methanesulfonate (MSA) with D/I water (18.3 $\text{M}\Omega\text{-cm}$)
 - For Sn-Cu alloy, 953 mg/L of Cu^{+2} methanesulfonate added
 - Current density 60 mA/cm^2 @ 25 $^{\circ}\text{C}$
 - 100 rpm rotating cathode
 - 99.999% Sn sheet anode

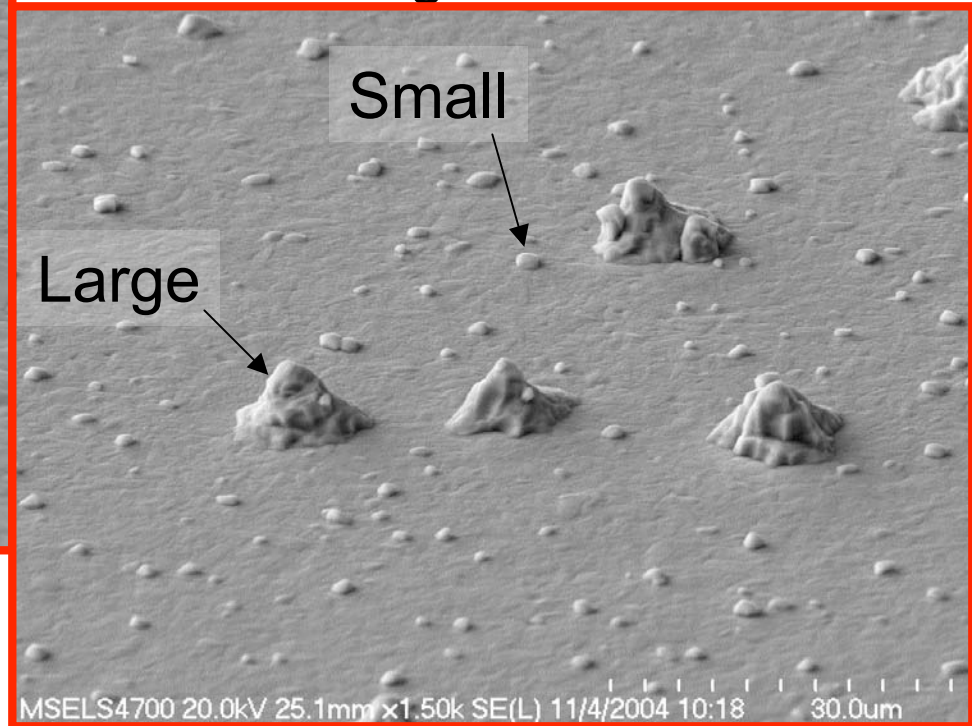
Crystallographic Orientation of Sn deposits & Hillocks

16 μm pure Sn on phosphor bronze cantilever beam

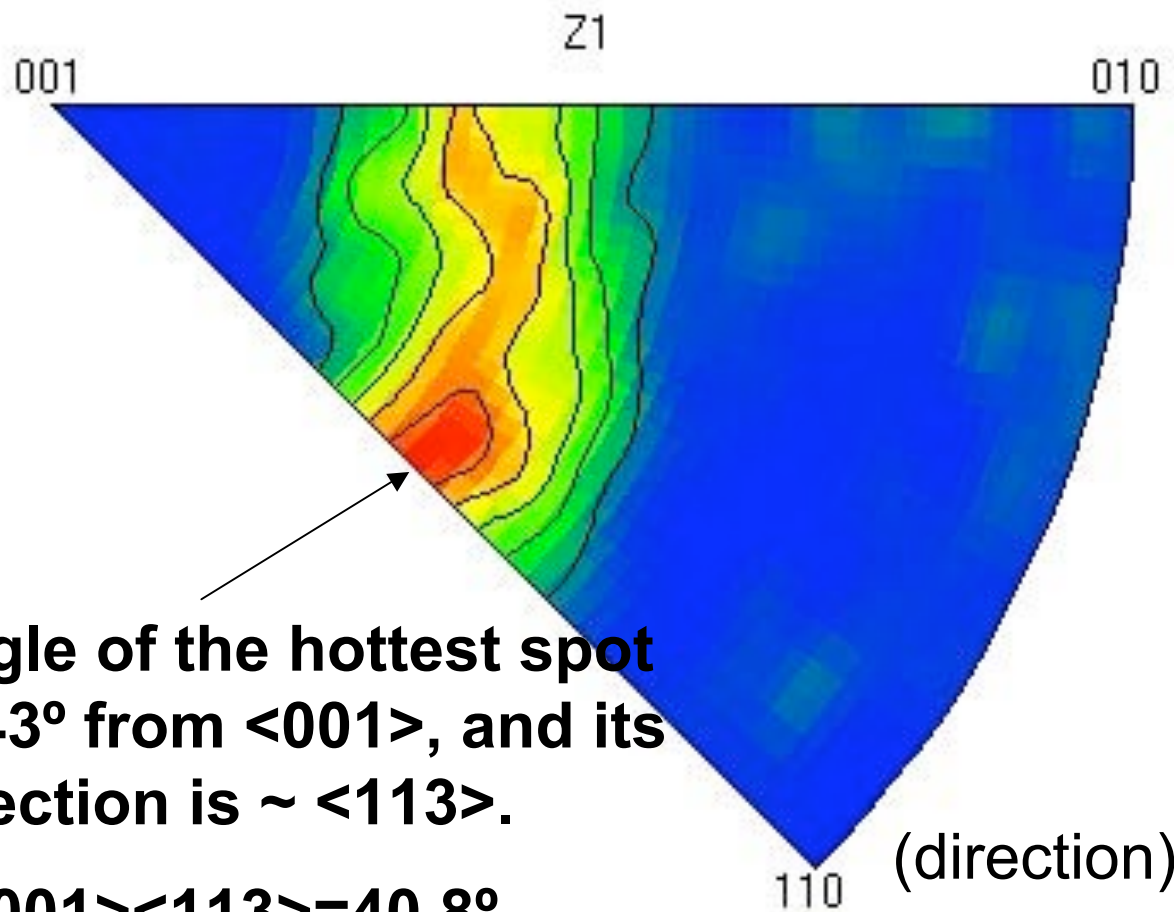
Bimodal distribution of
Hillocks: growth direction of
small & large measured



A measured area for grain
orientations: 3 places



Preferred orientation growth direction $\langle hkl \rangle$



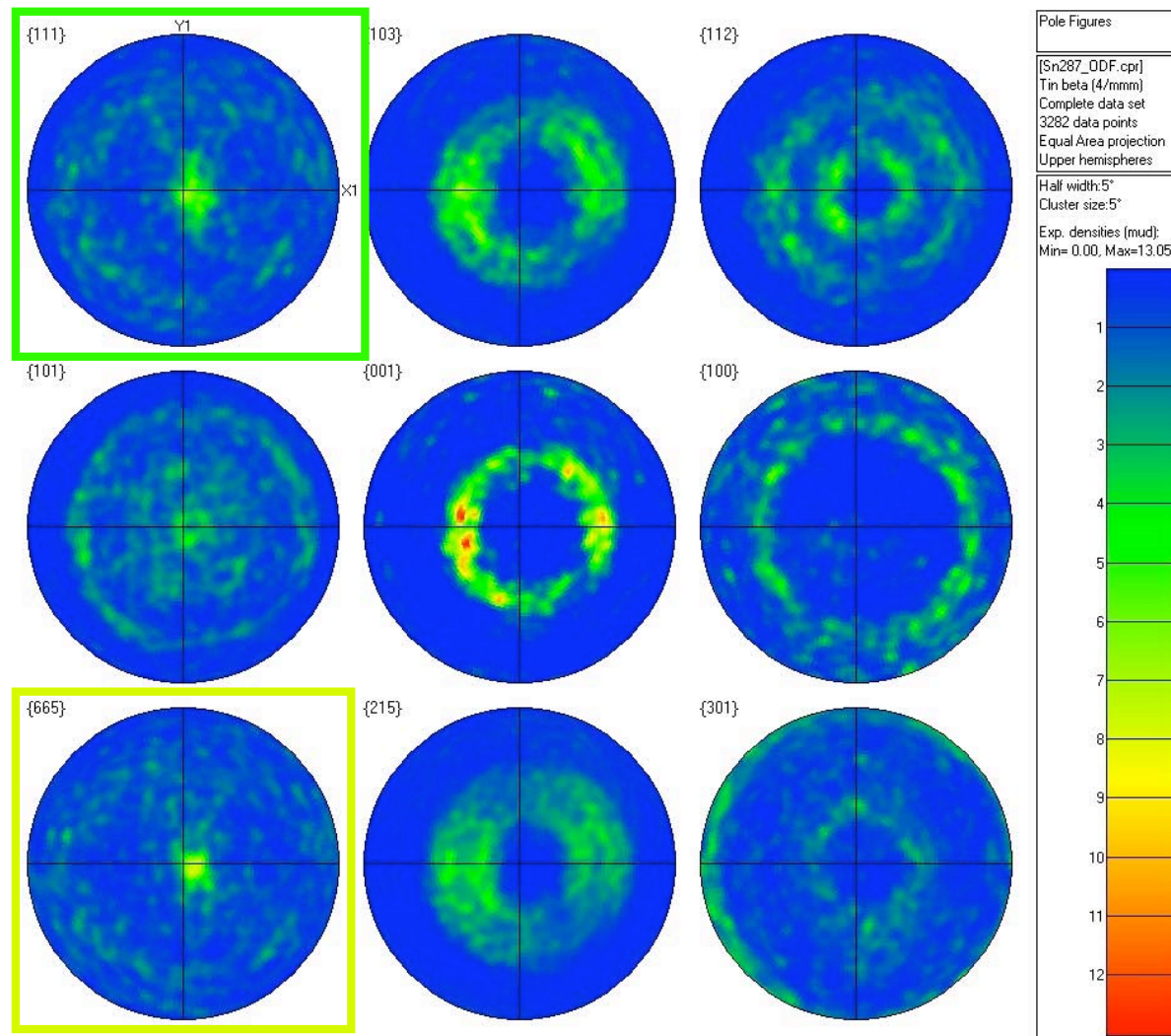
Angle of the hottest spot is 43° from $\langle 001 \rangle$, and its direction is $\sim \langle 113 \rangle$.

$\angle \langle 001 \rangle \langle 113 \rangle = 40.8^\circ$

Z1: normal direction to the sample surface

Inverse Pole Figure (Folded)	
[Sn287_ODF.cpr]	
Tin beta (4/mmm)	
Complete data set	
3282 data points	
Equal Area projection	
Upper hemisphere	
Half width: 5°	
Cluster size: 3°	
Exp. densities (mud):	
Min= 0.02, Max= 5.65	
1	—
2	—
3	—
4	—
5	—
1	—
2	—
3	—
4	—
5	—

Preferred orientation plane (hkl)



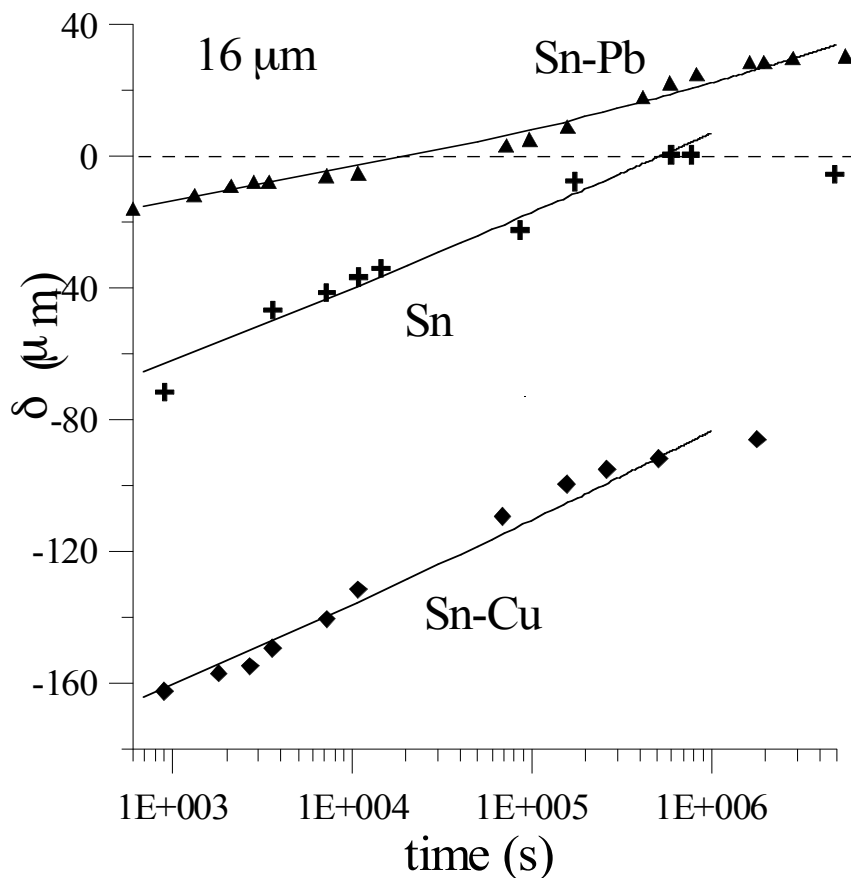
Sn(665) and Sn(111) planes show the most preferred orientation.

$$\angle(665)(001)=42.8^\circ$$

$$\angle(111)(001)=37.7^\circ$$

$$* (665) \perp \langle 113 \rangle$$

16 μm thick Sn and Sn alloy cantilever beam tests

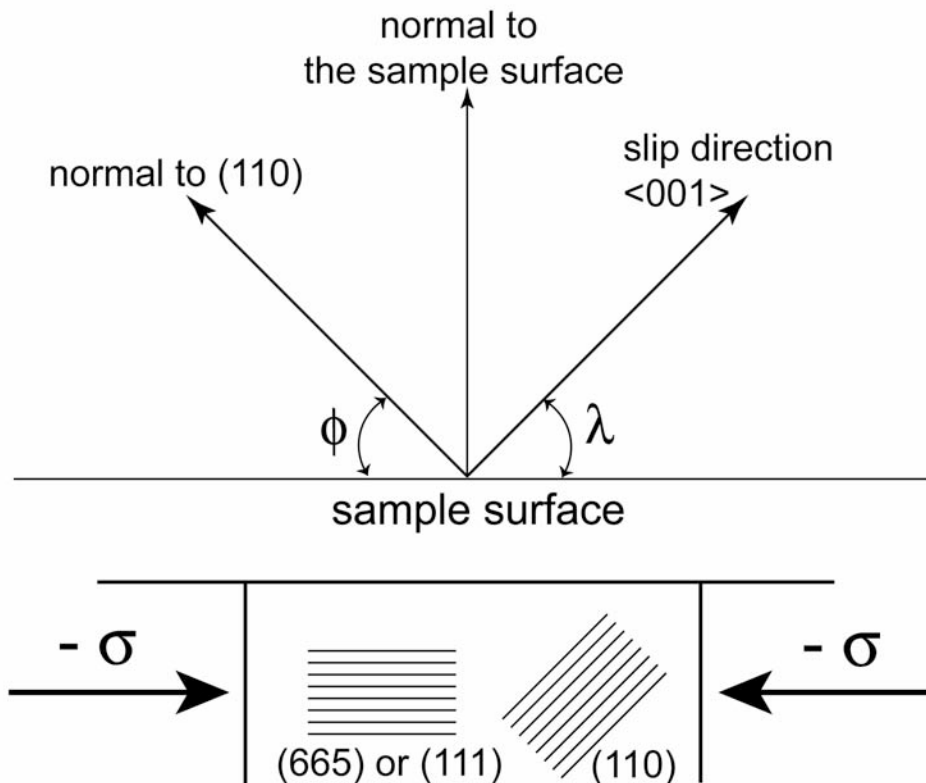


Bright Sn and Sn alloy electrodeposits show instantly compressive stress after deposition, and they release their stresses as a function of time by localized Nabarro-Herring-Coble creep.



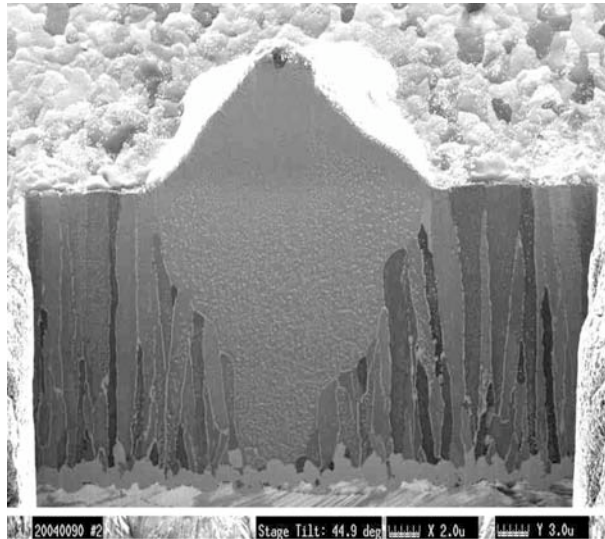
i.e., compressed during deposition

Bright Sn deposits may grow as a texture in order to reduce strain energy by slip from a high stress level of bright Sn deposition at 25 °C that is 0.59 T/T_m of Sn.

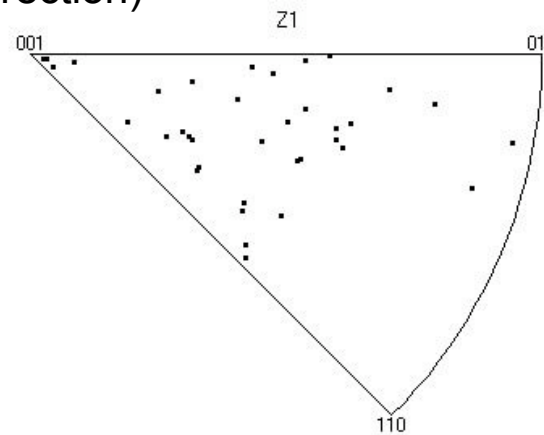


Schmid Factor: $SF = \cos \lambda \cdot \cos \phi$

- **Primary slip system of Sn: (110) $\langle 001 \rangle$ @ R.T.** (E.Schimid and W.Boas, *Plasticity of Crystals*, Chapman and Hall LTD., London, (1968))
- **Observed orientation has very easy slip since these preferred orientations have a high number of the Schmid factor. ($SF_{\max} = 0.5$)**
- **For example,**
 - For Sn(665), $\phi = 42.8^\circ$; $\lambda = 47.2^\circ$; and $SF = 0.49$
 - For Sn(111), $\phi = 37.7^\circ$; $\lambda = 52.3^\circ$; and $SF = 0.48$

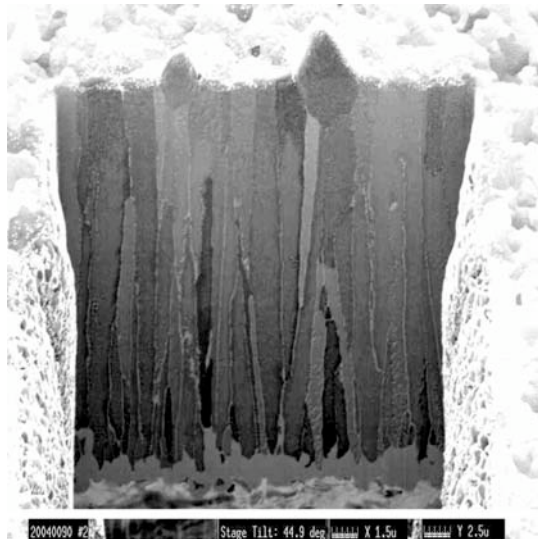


(direction)

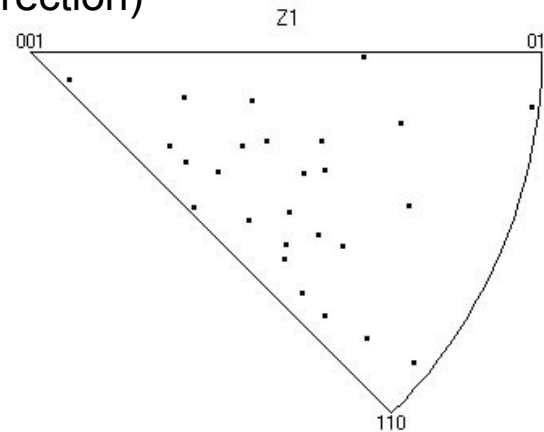


Inverse Pole Figure
(Folded)
[Regular_Bump_B.cpr]
Tin beta (4/mmm)
Complete data set
36 data points
Equal Area projection
Upper hemisphere

Large hillock: ~ 15 μm



(direction)

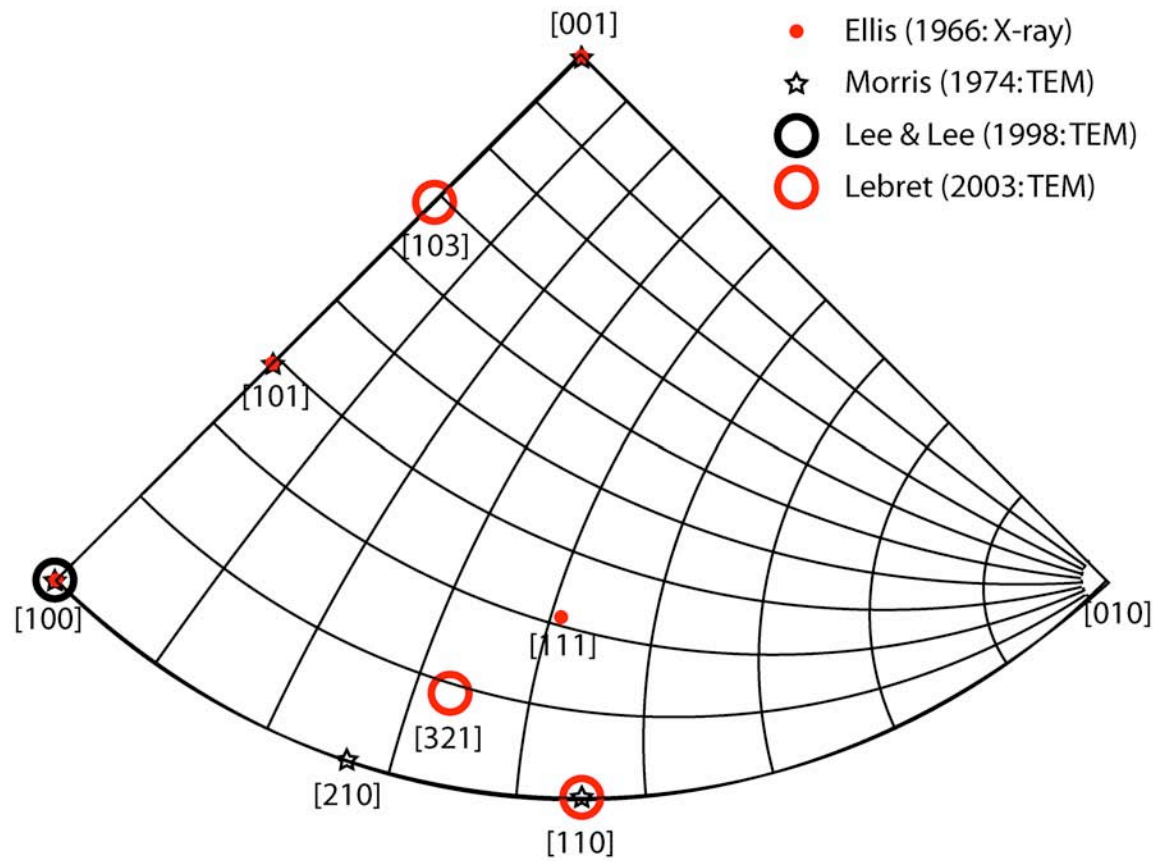


Inverse Pole Figure
(Folded)
[Small_Bump_A.cpr]
Tin beta (4/mmm)
Complete data set
26 data points
Equal Area projection
Upper hemisphere

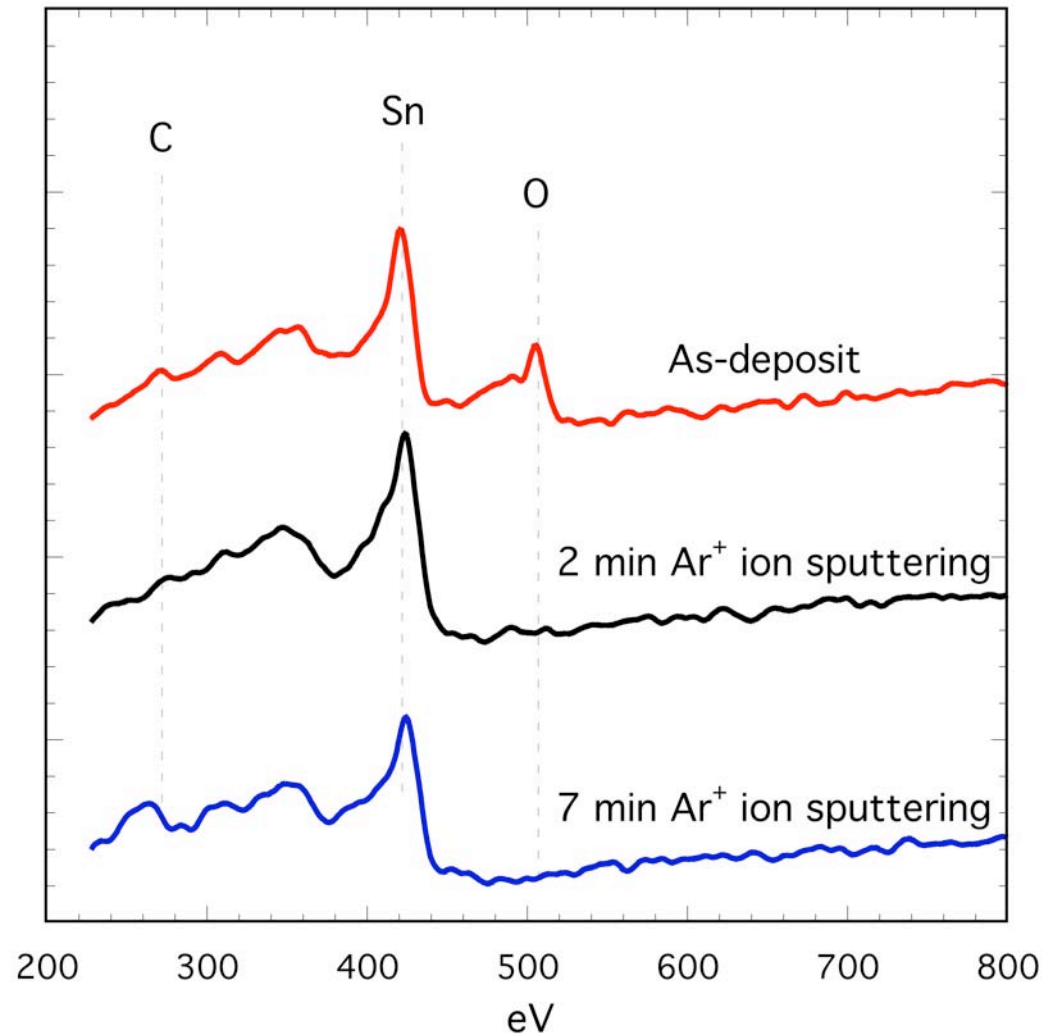
Small hillock: ~ 2 μm

Courtesy: G. Galyon and L. Palmer, IBM

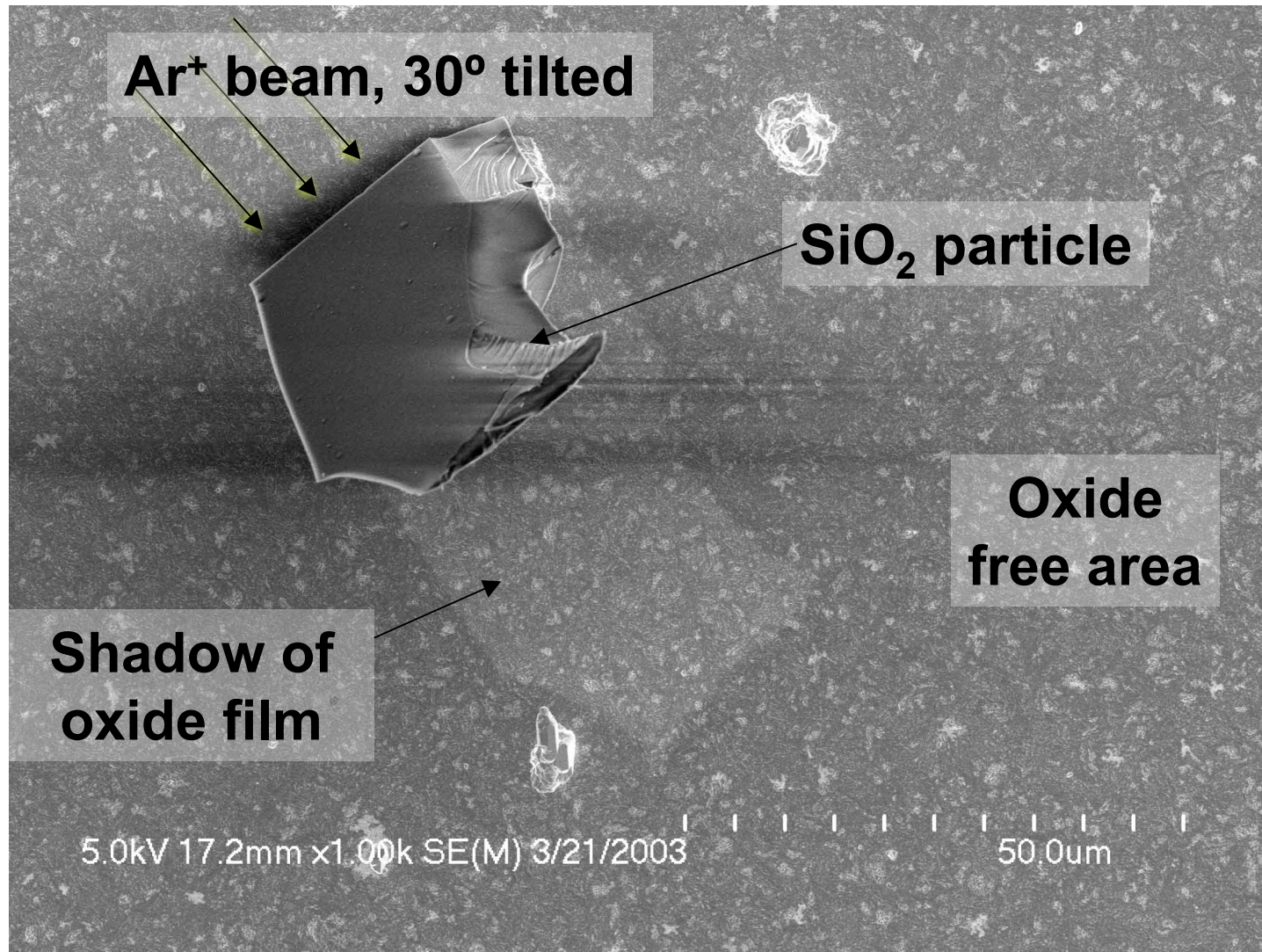
Sn deposits show a strong texture; nevertheless, hillock growth direction is scattered, which agrees with widely varied reports of whisker growth direction.

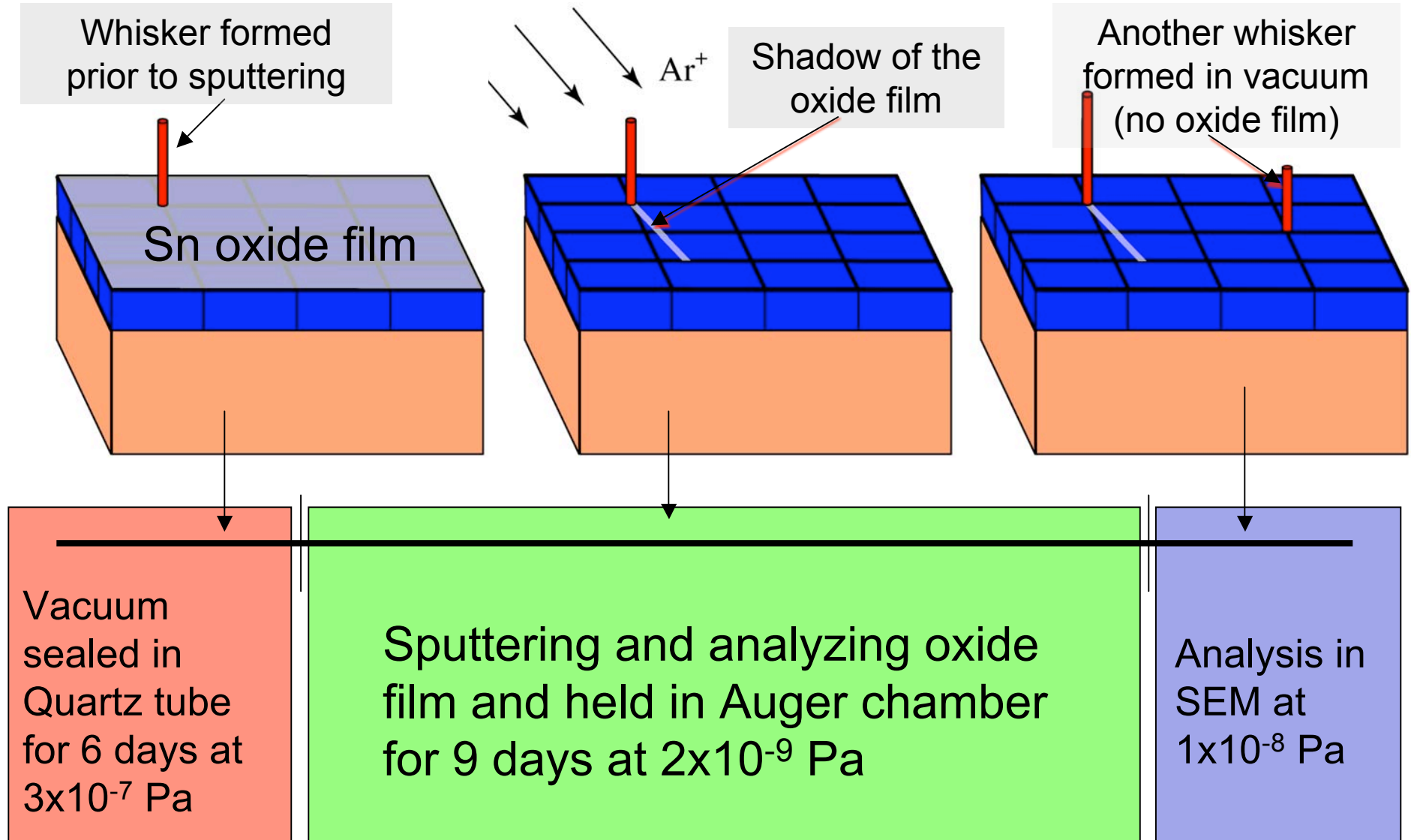


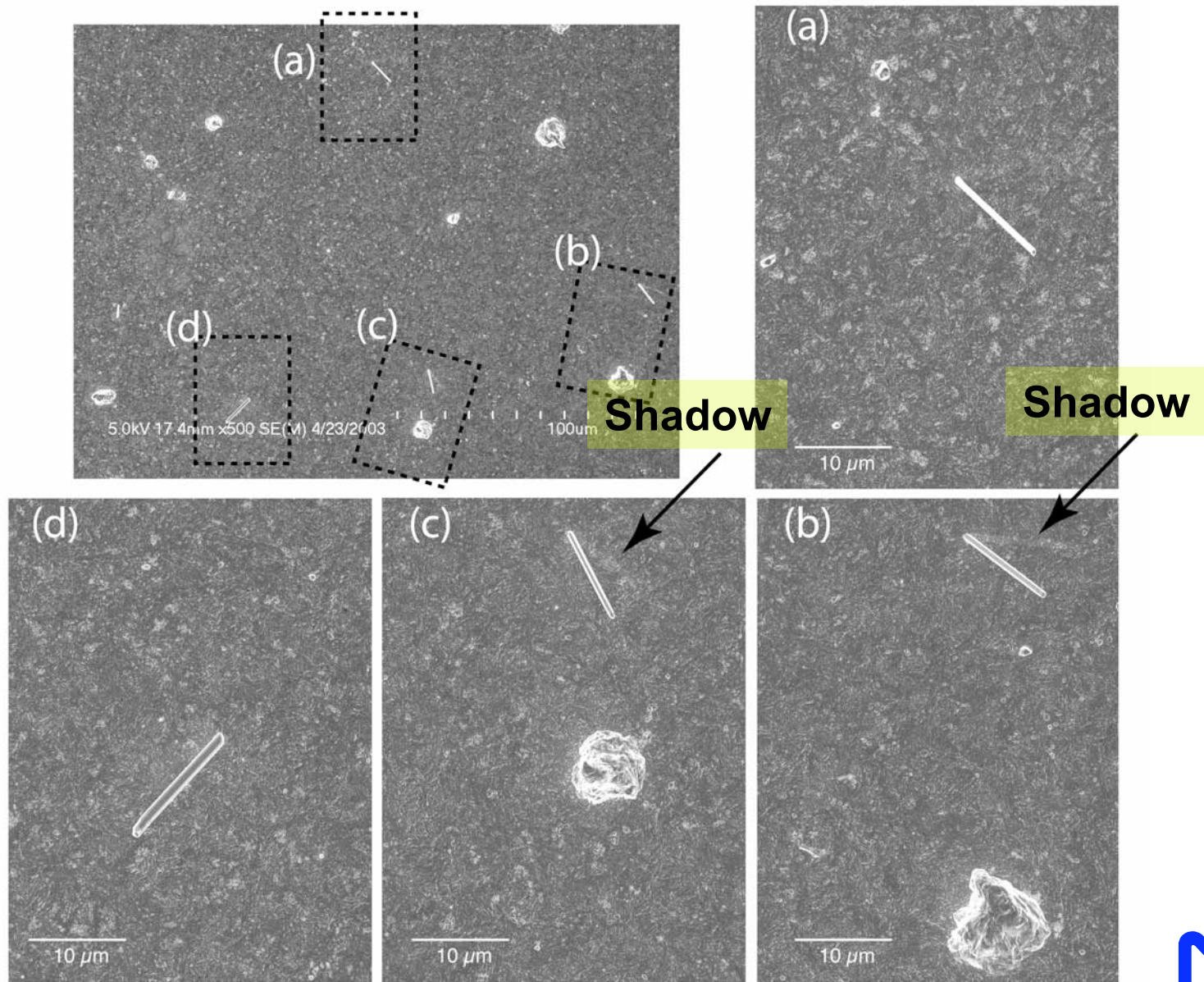
Effect of the Surface Oxide Film on Whisker Growth: Sn-3wt%Cu Deposit

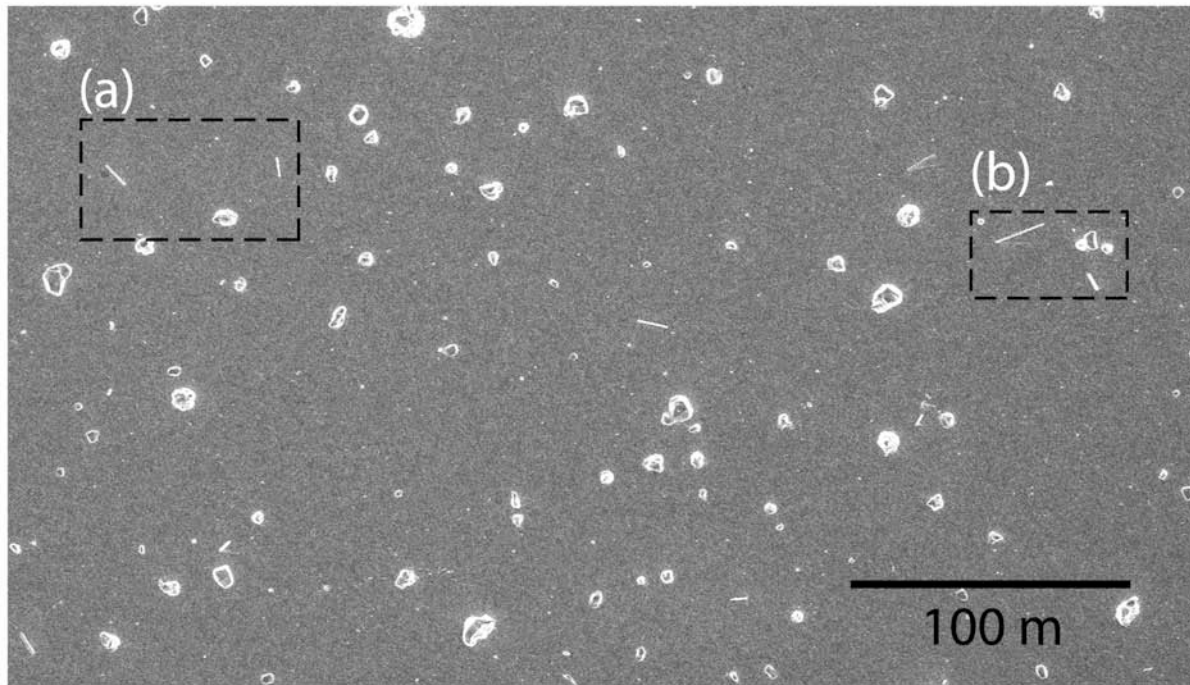


- **Plated and sealed in a quartz tube with an ultra high vacuum 3×10^{-7} Pa before Auger analysis.**
- **After 7 min of Ar^+ sputtering, Sn oxide surface film was eliminated successfully.**

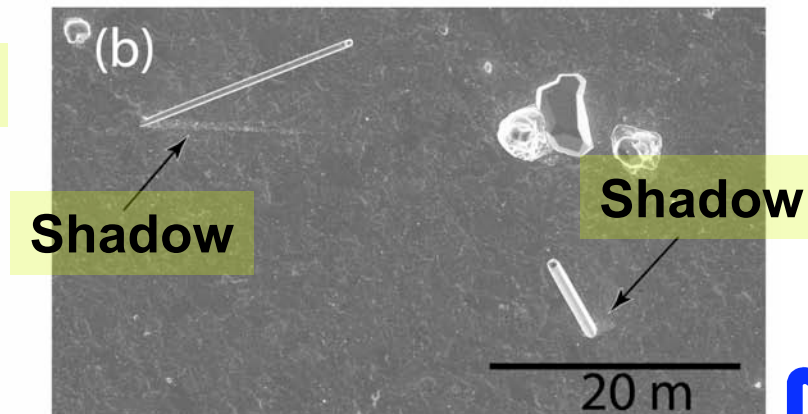
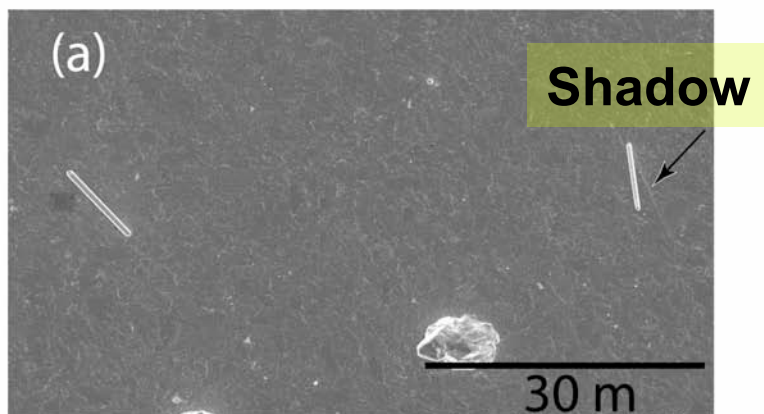








Sn whiskers are growing even after removing the Sn oxide film, which implies that there is little influence of oxide film



- **Base on EBSD analysis of bright Sn electrodeposits on phosphor bronze cantilever beams, deposit growth direction is $\langle 113 \rangle$, and preferred orientations of grains are (665) and (111). This result may be a response to reduce strain energy by easy slip to a high stress level during bright Sn deposition. Nevertheless, hillocks show a scattered growth direction regardless of a strong textured deposit.**
- **In order to test the effect of Sn surface oxide film on Sn whisker growth, Sn-3 wt%Cu alloy on pyrophosphate copper was analyzed by Auger & SEM. Sn whiskers grow even after removing the oxide film, which implies that there is little influence of the oxide film on whisker growth.**